

REMARKS

New claim 4, the only pending claim, has been added. Care has been exercised to avoid the introduction of new matter. Indeed, adequate descriptive support for the present Amendment should be apparent throughout the originally filed disclosure as, for example, Figs. 3B-3E, 8A, and 8B, and the related discussion thereof in the written description of the specification, noting page 1, lines 15 through 18 and page 7, lines 1 through 23. Applicants submit that the present Amendment does not generate any new matter issue.

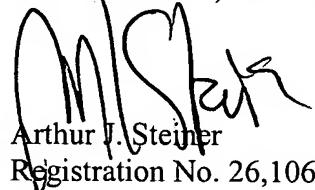
Applicants submit that claim 4 distinguishes over the prior art of record. In carrying out the method defined in independent claim 4, a semiconductor device having the structure illustrated in Fig. 1 is obtained. That illustrated structure comprises a silicon nitride film for preventing ions from penetrating through the isolation film, and prevents short circuiting due to misalignment of the contact formed on the embedded oxide film in a well controlled manner, as disclosed at page 4 the written description of the specification, lines 26 through 33. Accordingly, the claimed method significantly enhances miniaturization.

Based upon the foregoing, Applicants submit that claim 1 is in condition for immediate allowance. Favorable consideration is, therefore, respectfully solicited.

To the extent necessary, a petition for an extension of time under 37 C.F.R. 1.136 is hereby made. Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

MCDERMOTT, WILL & EMERY



Arthur J. Steiner
Registration No. 26,106

600 13th Street, N.W.
Washington, DC 20005-3096
(202) 756-8000 AJS:MWE:prg
Facsimile: (202) 756-8087
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